

1000V N-Channel MOSFET

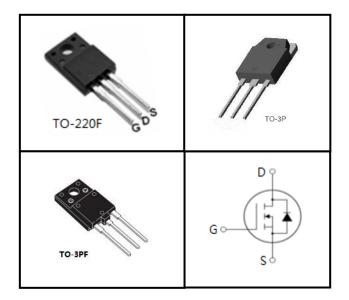
FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	Package	Marking		
CS4N100F	TO-220F	CS4N100F		
CS4N100V	TO-3P	CS4N100V		
CS4N100VF	TO-3PF	CS4N100VF		



Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
Parameter	Symbol	Value			Unit
Farameter		TO-220F	TO-3P	TO-3PF	Unit
Drain-Source Voltage ($V_{GS} = 0V$)	V _{DSS}	1000			V
Continuous Drain Current	I _D	4			A
Pulsed Drain Current (note1)	I _{DM}	16		A	
Gate-Source Voltage	V _{GSS}	±30		V	
Single Pulse Avalanche Energy (note2)	E _{AS}	88		mJ	
Avalanche Current (note1)	I _{AS}	4.2		A	
Repetitive Avalanche Energy (note1)	E _{AR}	52		mJ	
Power Dissipation (T _C = 25°C)	P _D	36	7	′ 5	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C	

Thermal Resistance					
Barrandar	Symbol	Value			
Parameter		TO-220F	TO-3P	TO-3PF	- Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	3.47	1.67		00/14/
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60		°C/W



CS4N100F,CS4N100V,CS4N100VF

Specifications $T_J = 25^{\circ}C$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
Falameter	Symbol	Test conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	1000			V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 1000V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 30V$			±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_{D} = 2.0A$		3.6	4.3	Ω
Dynamic						
Input Capacitance	C _{iss}	$\mathcal{V} = \mathcal{O}\mathcal{V}$		689		
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$		68		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		13		
Total Gate Charge	Q _g			27		
Gate-Source Charge	Q _{gs}	$V_{DD} = 800V, I_D = 4.0A, V_{GS} = 10V$		4		nC
Gate-Drain Charge	Q_{gd}			12		
Turn-on Delay Time	t _{d(on)}			37		
Turn-on Rise Time	t _r	V _{DD} = 500V, I _D =4.0A,		16		
Turn-off Delay Time	t _{d(off)}	$V_{\text{DD}} = 500\text{V}, \text{ I}_{\text{D}} = 4.0\text{A},$ $\text{R}_{\text{G}} = 25 \ \Omega$		145		ns
Turn-off Fall Time	t _f			37		
Drain-Source Body Diode Character	istics					
Continuous Body Diode Current	۱ _s	T 0500			4	
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			16	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 2.0A, V _{GS} = 0V			1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 4.0A,		980		ns
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /µs		1.6		μC

Notes

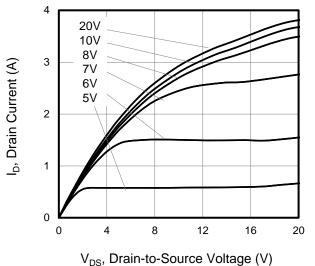
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 10.0mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%



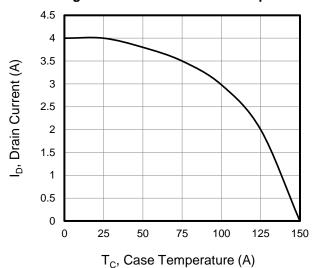
Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

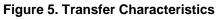
Figure 1. Output Characteristics (T_J = 25°C)

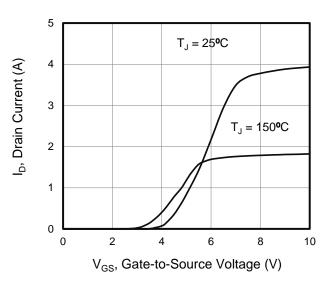












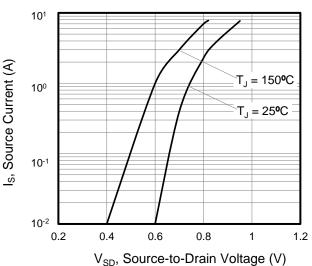
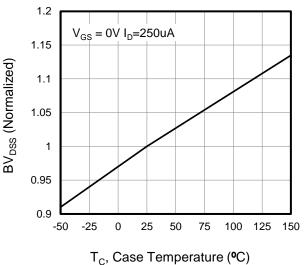
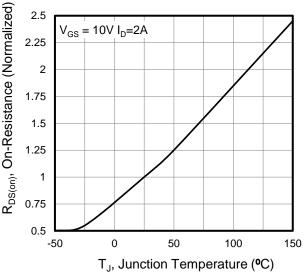


Figure 4. BV_{DSS} Variation vs. Temperature









Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

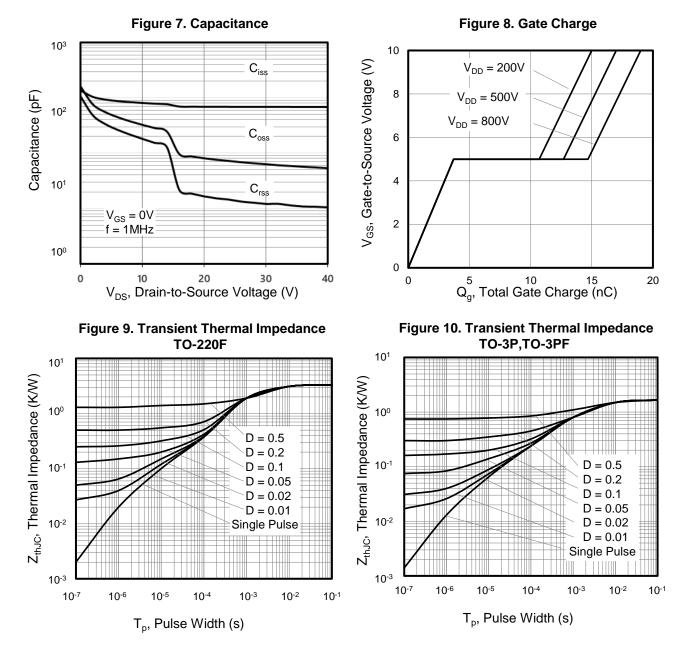




Figure A: Gate Charge Test Circuit and Waveform

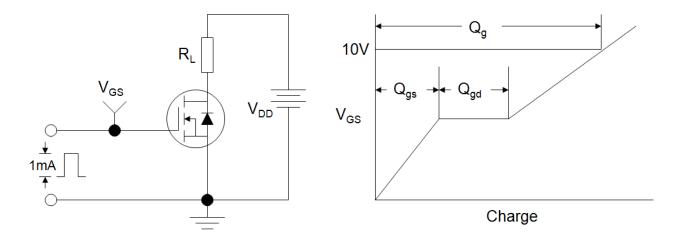


Figure B: Resistive Switching Test Circuit and Waveform

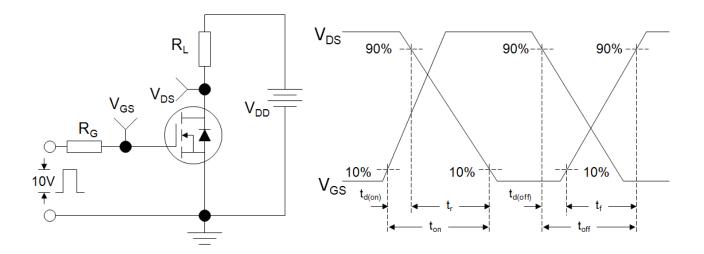
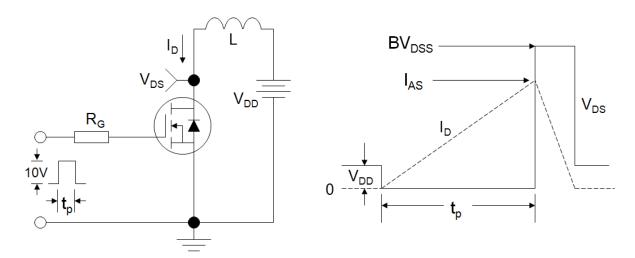


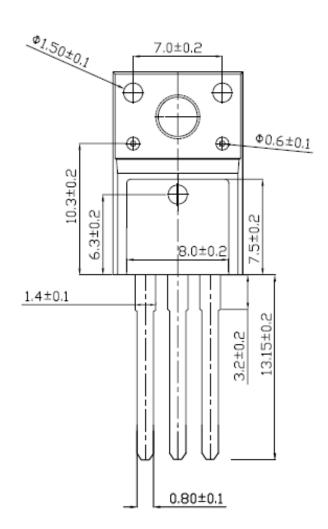
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

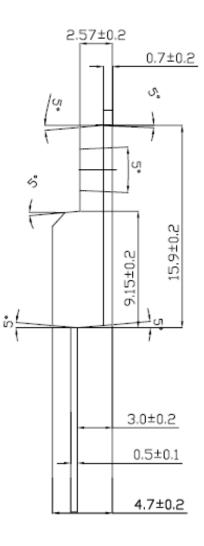


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TO-220F

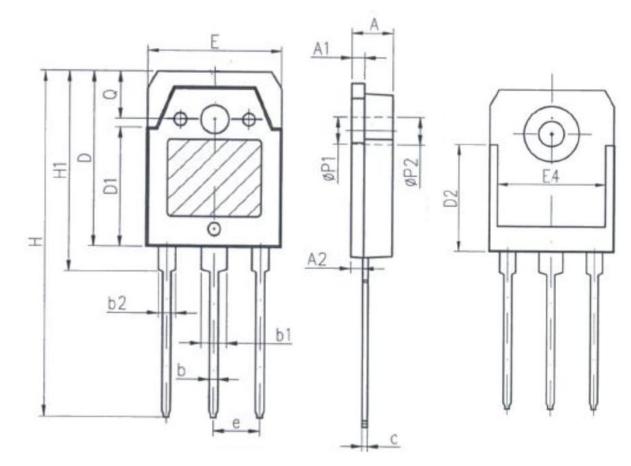






CS4N100F,CS4N100V,CS4N100VF

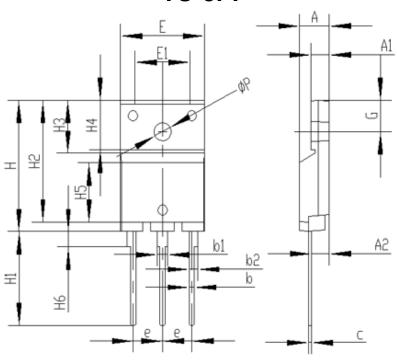
TO-3P



Unit:mm				
Symbol	Min.	Max.		
Α	4.6	5		
A1	1.4	1.65		
A2	1.18	1. 58		
b	0.8	1.2		
b1	2.8	3.2		
b2	1.8	2.2		
с	0.5	0.75		
D	19.6	20.2		
D1	13.55	14. 25		
D2	12. 9	PREF		
E	15.35	15.85		
E4	12.6	-		
е	5. 45TYP			
Н	40.1	40.9		
H1	23.15	23.65		
P1	3. 2REF			
P2	3. 5REF			



TO-3PF





Cumhal	单位 mm			
Symbol	Min	Nom	Max	
Α	5.30	5.50	5.70	
A1	3.30	3.50	3.70	
A2	3.20	3.40	3.60	
b	0.80	1.0	1.20	
b1	1.80	2.00	2.20	
b 2	1.40	1.60	1.80	
С	0.40	0.50	0.60	
е	5.25	5.45	5.65	
E	15.4	15.6	15.8	
E1	10.0	10.2	10.4	
Н	22.8	23.0	23. 2	
H1	16.0	16.5	17.0	
H2	21.2	21.4	21.6	
H3	9.10	9.30	9.50	
H4	8.55	8.75	8.95	
H5	10.2	10.4	10.6	
H6	2.55	2.70	2.85	
G	5.3	5.5	5.7	
ΦΡ	3.00	3.20	3.40	



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